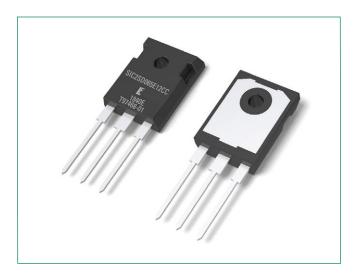


LSIC2SD065E12CCA 650 V, 12 A SiC Schottky Barrier Diode





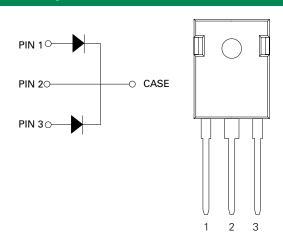
Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C. maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Circuit Diagram TO-247-3L



Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF**Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating



Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	650	V	
DC Blocking Voltage	V _R	T _J = 25 °C	650	V	
Continuous Forward Current (Per Leg/Component)	I _F	T _c = 25 °C	18.5 / 37	А	
		T _C = 152 °C	6 / 12		
Non-Repetitive Forward Surge Current (Per Leg)	FSM	$T_{\rm c}$ = 25 °C, $t_{\rm p}$ = 10 ms, Half sine pulse	32	А	
Power Dissipation (Per Leg/Component)	P _{Tot}	T _c = 25 °C	75 / 150	W	
		T _C = 110 °C	32 / 64		
Operating Junction Temperature	T _J	-	-55 to 175	°C	
Storage Temperature	T _{stg}	-	-55 to 150	°C	
Soldering Temperature	T _{sold}	-	260	°C	

Electrical Characteristics (T_J = 25 °C unless otherwise specified)

Characteristics Symb	Comphal	l Conditions	Value			Unit	
	Symbol		Min.	Тур.	Max.	Unit	
Forward Voltage	V _F	I _F = 6 A, T _J = 25 °C	-	1.5	1.8	V	
		I _F = 6 A, T _J = 175 °C	-	1.85	-		
Reverse Current I _R		$V_{R} = 650 \text{ V, } T_{J} = 25 ^{\circ}\text{C}$	-	<1	50		
	I _R	V _R = 650 V, T _J = 175 °C	-	15	-	μΑ	
Total Capacitance C		$V_R = 1 \text{ V, f} = 1 \text{ MHz}$	-	300	-		
	С	V _R = 200 V, f = 1 MHz	-	39	-	pF	
		V _R = 400 V, f = 1 MHz	-	28	-		
Total Capacitive Charge	Q _c	$V_{R} = 400 \text{ V}, Q_{c} = \int_{C}^{V_{R}} C(V) dV$	-	20	-	nC	

Thermal Characteristics

Characteristics	Symbol	Value	Unit
Thermal Resistance (Per Leg/Component)	Reic	2 / 1	°C/W

Figure 1: Typical Foward Characteristics

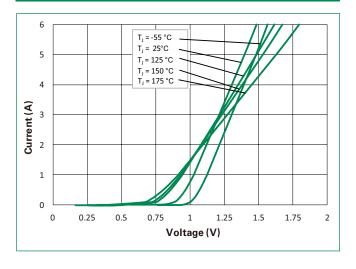


Figure 2: Typical Reverse Characteristics

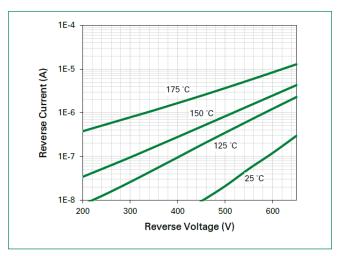




Figure 3: Power Derating

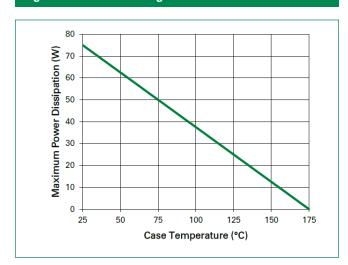


Figure 4: Current Derating

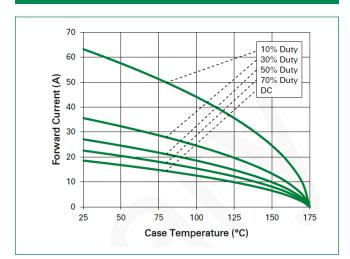


Figure 5: Capacitance vs. Reverse Voltage

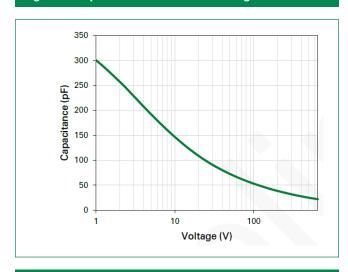


Figure 6: Capacitive Charge vs. Reverse Voltage

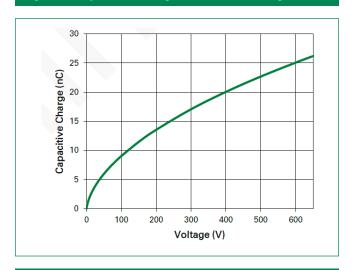


Figure 7: Stored Energy vs. Reverse Voltage

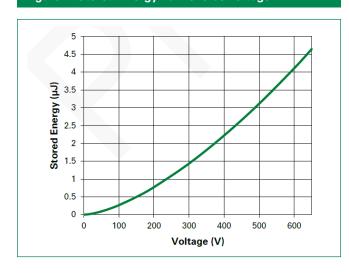
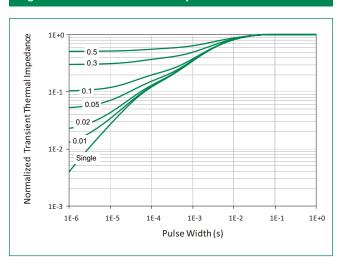
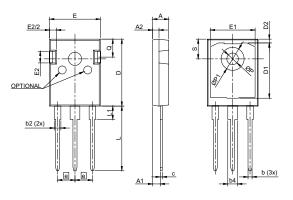


Figure 8: Transient Thermal Impedance



GEN2 SiC Schottky Diode LSIC2SD065E12CCA, 650 V, 12 A, T0-247-3L

Package Dimensions TO-247-3L



Recommended Hole Pattern Layout



Notes:

1. Dimensions are in millimeters

2. Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These measured at the outermost extreme of plastic body.

3.eP to have a maximum draft angle of 1.5" to the top of the part with a maximum hole diameter of 0.154"

Symbol	Millimeters			
	Min	Nom	Max	
Α	4.80	5.03	5.20	
A1	2.25	2.38	2.54	
A2	1.85	1.98	2.11	
b	0.99	-	1.40	
b2	1.65	-	2.39	
b4	2.59	-	3.43	
С	0.38	0.64	0.89	
D	20.80	20.96	21.34	
D1	13.50	-	-	
D2	0.51	1.19	1.35	
е	5.44 BSC			
E	15.75	15.90	16.13	
E1	13.06	14.02	14.15	
E2	4.19	4.32	4.83	
L	19.81	20.19	20.57	
L1	3.81	4.19	4.45	
øΡ	3.55	3.61	3.66	
øP1	7.06	7.19	7.32	
Q	5.49	5.61	6.20	
S	6.05	6.17	6.30	

Part Numbering and Marking System



SIC = SiC = Gen2 2

SD = Schottky Diode = Voltage Rating (650 V) 065

Ε = TO-247-3L

12 = Current Rating (12 A) CC = Common Cathode

ΥY = Year

= Week WW

Χ = Trace Code (Any Letter)

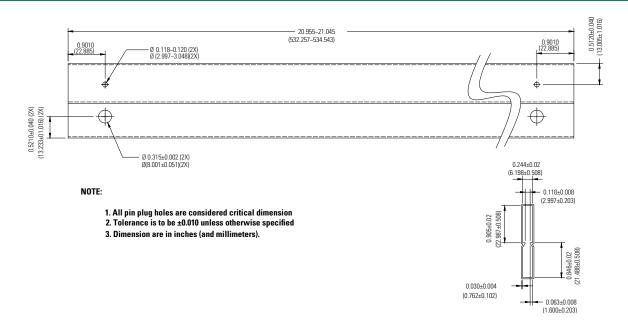
ZZZZZZ-ZZ = Lot Number

Packing Options

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD065E12CCA	SIC2SD065E12CC	Tube (30pcs)	450

GEN2 SiC Schottky Diode LSIC2SD065E12CCA, 650 V, 12 A, T0-247-3L

Packing Specification TO-247-3L



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